

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of the claims in the application:

Listing of Claims

1. (previously presented) An image sensor comprising a matrix of solid-state light sensor elements, each of which represents a unit pixel and is capable of reading out in a time series sensor signals of respective pixels by sequentially selecting pixel lines one by one and sequentially selecting sensor signals one by one in a selected pixel line, characterized in that each of the pixel lines is evenly divided into a plurality of blocks with each block composed of a specified number of pixels, a first scanning means is provided for sequentially reading out pixel sensor signals on a block-by-block basis starting from a first block, a buffer means is provided for temporally storing pixel sensor signals of a readout block, a second scanning means is provided for sequentially reading out pixel sensor signals on a pixel-by-pixel basis from a selected block and a bias circuit is provided for converting a pixel sensor signal scanned by the first scanning means into a voltage value by using a reference resistance with a bias voltage applied thereto,

wherein the first scanning means comprises a pixel selecting circuit (2) for providing signals for sequentially selecting pixels on the line-by-line basis and a switch circuit (3) for outputting sensor signals according to the pixel selecting signals from the pixel selecting circuit, and the second scanning means comprises a pixel selecting circuit (7) for providing a signal for sequentially selecting pixels on the block-by-block basis and a switch circuit (8) for outputting sensor signals according to the pixel selecting signals from the pixel selecting circuit.

2. (canceled)

3. (previously presented) An image sensor as defined in claim 1, characterized in that the pixel selecting circuits of the first scanning means and the

second scanning means are composed each of a shift register circuit or a decoder circuit.

4. (previously presented) An image sensor as defined in claim 1, characterized in that the duration of a pixel selecting signal provided by the first scanning means corresponds to a time necessary for selecting pixels of one block.

5. (original) An image sensor as defined in claim 1, characterized in that the solid-state light sensor element is a light sensor circuit which is capable of producing in a photoelectric converting element a sensor current proportional to the quantity of light falling thereon, converting the sensor current into a voltage signal by a transistor with a logarithmic output characteristic in a weak inverse state, and outputting a sensor signal corresponding to the voltage signal.

6. (original) An image sensor as defined in claim 5, characterized in that the light sensor circuit is initialized before detecting light by removing an electric charge remaining in a parasitic capacitor of the photoelectric converting element by changing a drain voltage of a MOS type transistor having a logarithmic output characteristic in a weak inverse state lower than a normal working value.

7-15. (canceled)

16. (currently amended) A method of scanning the pixels of an image sensor comprised of a matrix of solid-state light sensor elements, each of which represents a unit pixel and is capable of reading out in a time series sensor signals of respective pixels by sequentially selecting pixel lines one by one and sequentially selecting sensor signals one by one in a selected pixel line, comprising the steps of dividing each of the pixel lines into a plurality of blocks with each block composed of a specified number of pixels, first scanning the pixels for sequentially reading out pixel sensor signals on a block-by-block basis starting from a first block, temporally storing the pixel sensor signals of a readout block, then scanning the pixels for sequentially reading out pixel sensor signals on a pixel-by-pixel basis from a selected block, and converting a pixel

sensor signal scanned in the first scanning step into a voltage value by using a reference resistance with a bias voltage applied thereto,

wherein the duration of a pixel selecting signal provided by the first scanning step corresponds to a time necessary for selecting pixels of one block, and

~~A method as defined in claim 14, characterized in that the solid-state light sensor element is a light sensor circuit which is capable of producing in a photoelectric converting element a sensor current proportional to the quantity of light falling thereon, converting the sensor current into a voltage signal by a transistor with a logarithmic output characteristic in a weak inverse state, and outputting a sensor signal corresponding to the voltage signal.~~

17. (original) A method as defined in claim 16, characterized in that the light sensor circuit is initialized before detecting light by removing an electric charge remaining in a parasitic capacitor of the photoelectric converting element by changing a drain voltage of a MOS type transistor having a logarithmic output characteristic in a weak inverse state lower than a normal working value.

18-22. (canceled)